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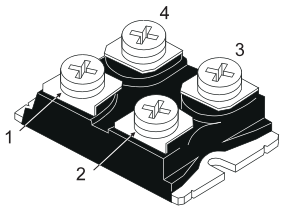
STE48NM60

N-CHANNEL 600V - 0.09Ω - 48A ISOTOP
MDmesh™ Power MOSFET

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STE48NM60	600V	< 0.11Ω	48 A

- TYPICAL $R_{DS}(on)$ = 0.09Ω
- HIGH dv/dt AND AVALANCHE CAPABILITIES
- 100% AVALANCHE TESTED
- LOW INPUT CAPACITANCE AND GATE CHARGE
- LOW GATE INPUT RESISTANCE
- TIGHT PROCESS CONTROL AND HIGH MANUFACTURING YIELDS



ISOTOP

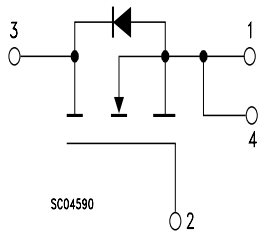
DESCRIPTION

The MDmesh™ is a new revolutionary MOSFET technology that associates the Multiple Drain process with the Company's PowerMESH™ horizontal layout. The resulting product has an outstanding low on-resistance, impressively high dv/dt and excellent avalanche characteristics. The adoption of the Company's proprietary strip technique yields overall dynamic performance that is significantly better than that of similar competition's products.

APPLICATIONS

The MDmesh™ family is very suitable for increasing power density of high voltage converters allowing system miniaturization and higher efficiencies.

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	600	V
V_{DGR}	Drain-gate Voltage (R_{GS} = 20 kΩ)	600	V
V_{GS}	Gate- source Voltage	±30	V
I_D	Drain Current (continuous) at T_C = 25°C	48	A
I_D	Drain Current (continuous) at T_C = 100°C	30	A
I_{DM} (•)	Drain Current (pulsed)	192	A
P_{TOT}	Total Dissipation at T_C = 25°C	450	W
	Derating Factor	3.57	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	15	V/ns
T_{stg}	Storage Temperature	–65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

(•)Pulse width limited by safe operating area

(1) I_{SD} ≤48A, di/dt ≤400A/µs, V_{DD} ≤ $V_{(BR)DSS}$, T_j ≤ $T_{JMAX.}$

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case	Max	0.28	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max	30	°C/W
T_l	Maximum Lead Temperature For Soldering Purpose		300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	15	A
E_{AS}	Single Pulse Avalanche Energy (starting T_j = 25 °C, $I_D = I_{AR}$, V_{DD} = 35 V)	850	mJ

ELECTRICAL CHARACTERISTICS (T_{CASE} = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 250 µA, V_{GS} = 0	600			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating			10	µA
		V_{DS} = Max Rating, T_C = 125 °C			100	µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ±30V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, I_D = 250µA	3	4	5	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10V, I_D = 22.5A		0.09	0.11	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$, I_D = 22.5A		15		S
C_{iss}	Input Capacitance	V_{DS} = 25V, f = 1 MHz, V_{GS} = 0		3800		pF
C_{oss}	Output Capacitance			1250		pF
C_{rss}	Reverse Transfer Capacitance			46		pF
$C_{oss\ eq.}$ (2)	Equivalent Output Capacitance	V_{GS} = 0V, V_{DS} = 0V to 480V		340		pF
R_G	Gate Input Resistance	f=1 MHz Gate DC Bias = 0 Test Signal Level = 20mV Open Drain		1.4		Ω

1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
2. $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

ELECTRICAL CHARACTERISTICS (CONTINUED)
SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	V_{DD} = 250V, I_D = 22.5A		30		ns
t_r	Rise Time	R_G = 4.7Ω V_{GS} = 10V (see test circuit, Figure 3)		20		ns
Q_g	Total Gate Charge	V_{DD} = 400V, I_D = 45A,		96	134	nC
Q_{gs}	Gate-Source Charge	V_{GS} = 10V		31		nC
Q_{gd}	Gate-Drain Charge			43		nC

SWITCHING OFF

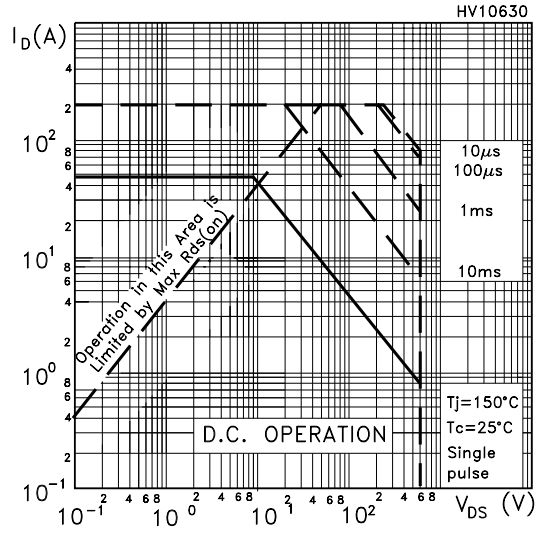
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	V_{DD} = 400V, I_D = 45A,		16		ns
t_f	Fall Time	R_G = 4.7Ω, V_{GS} = 10V (see test circuit, Figure 5)		23		ns
t_c	Cross-over Time			40		ns

SOURCE DRAIN DIODE

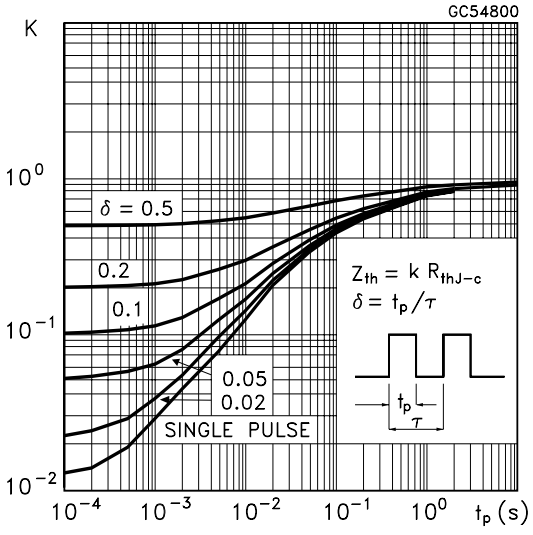
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				48	A
I_{SDM} (2)	Source-drain Current (pulsed)				192	A
V_{SD} (1)	Forward On Voltage	I_{SD} = 45A, V_{GS} = 0			1.5	V
t_{rr}	Reverse Recovery Time	I_{SD} = 45A, di/dt = 100A/µs,		508		ns
Q_{rr}	Reverse Recovery Charge	V_{DD} = 100 V, T_j = 25°C		10		µC
I_{RRM}	Reverse Recovery Current	(see test circuit, Figure 5)		40		A
t_{rr}	Reverse Recovery Time	I_{SD} = 45A, di/dt = 100A/µs,		650		ns
Q_{rr}	Reverse Recovery Charge	V_{DD} = 100 V, T_j = 150°C		14		µC
I_{RRM}	Reverse Recovery Current	(see test circuit, Figure 5)		43		A

Note: 1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

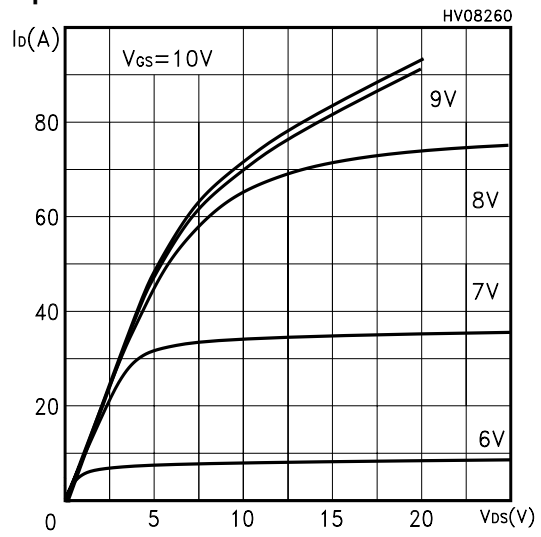
Safe Operating Area



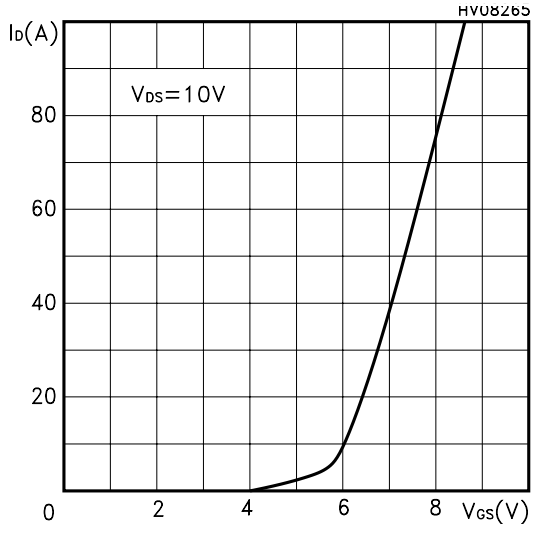
Thermal Impedance



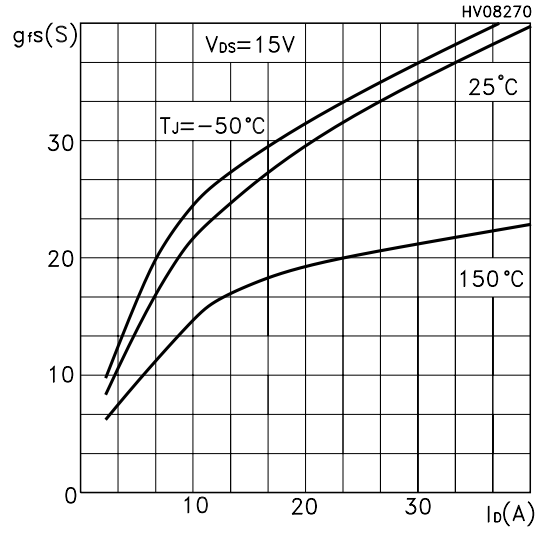
Output Characteristics



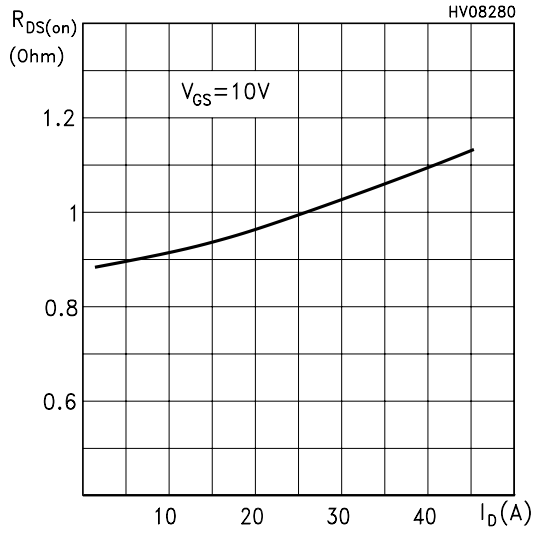
Transfer Characteristics



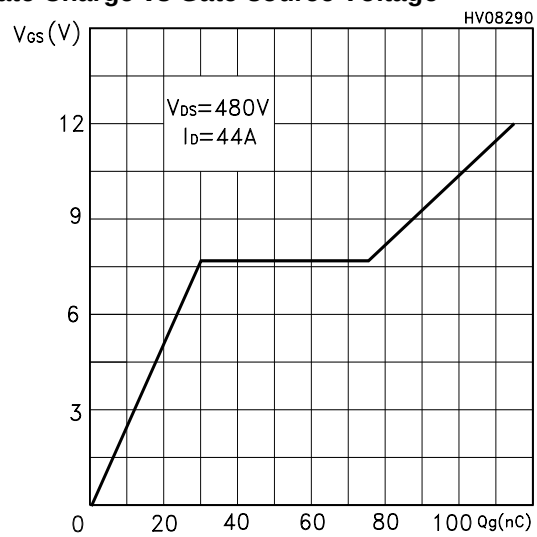
Transconductance



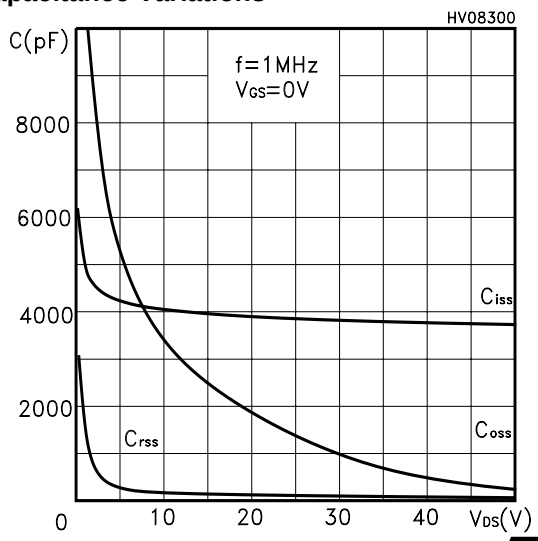
Static Drain-source On Resistance



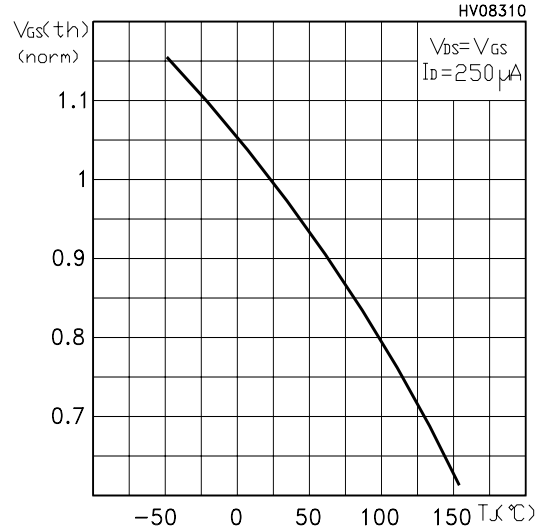
Gate Charge vs Gate-source Voltage



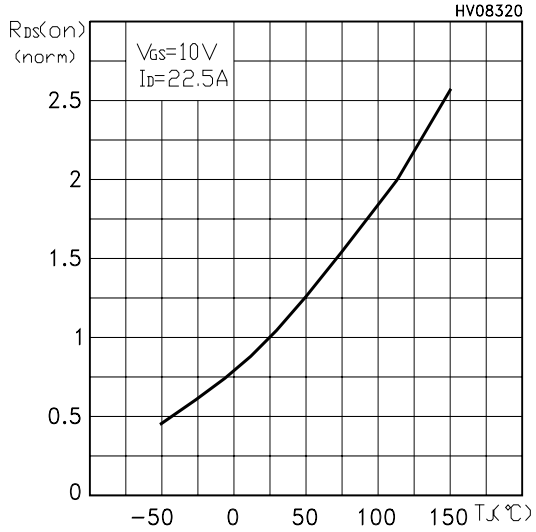
Capacitance Variations



Normalized Gate Thereshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

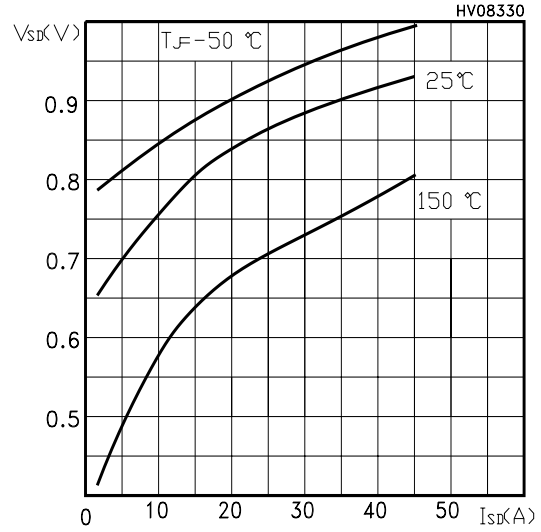


Fig. 1: Unclamped Inductive Load Test Circuit

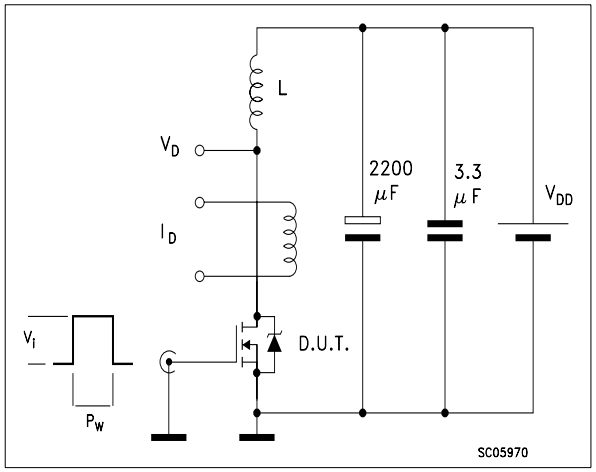


Fig. 2: Unclamped Inductive Waveform

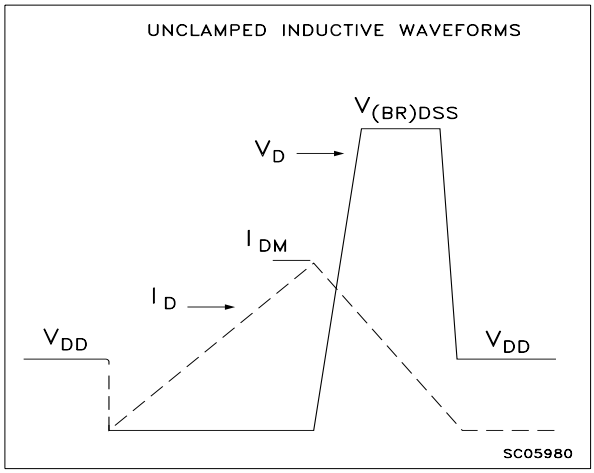


Fig. 3: Switching Times Test Circuit For Resistive Load

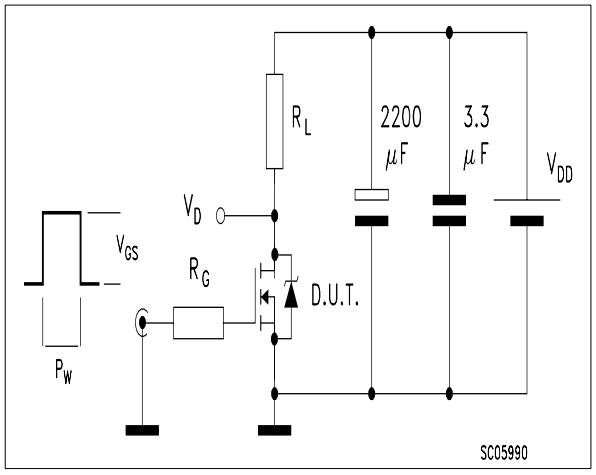


Fig. 4: Gate Charge test Circuit

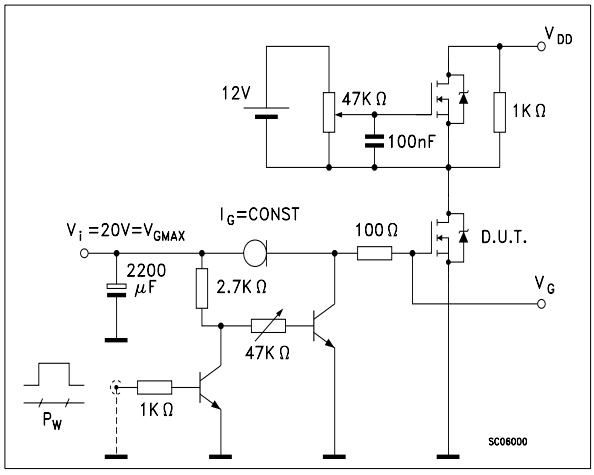
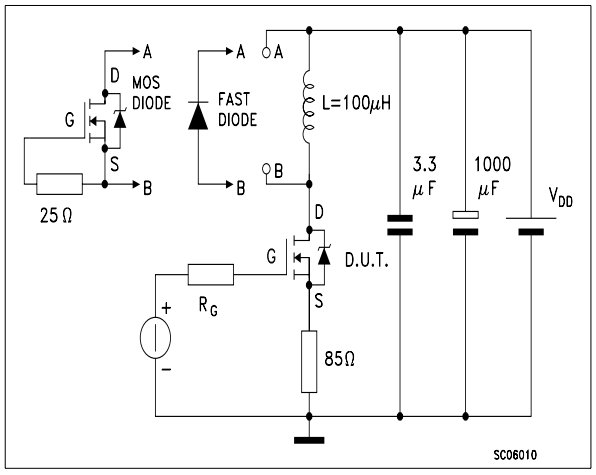
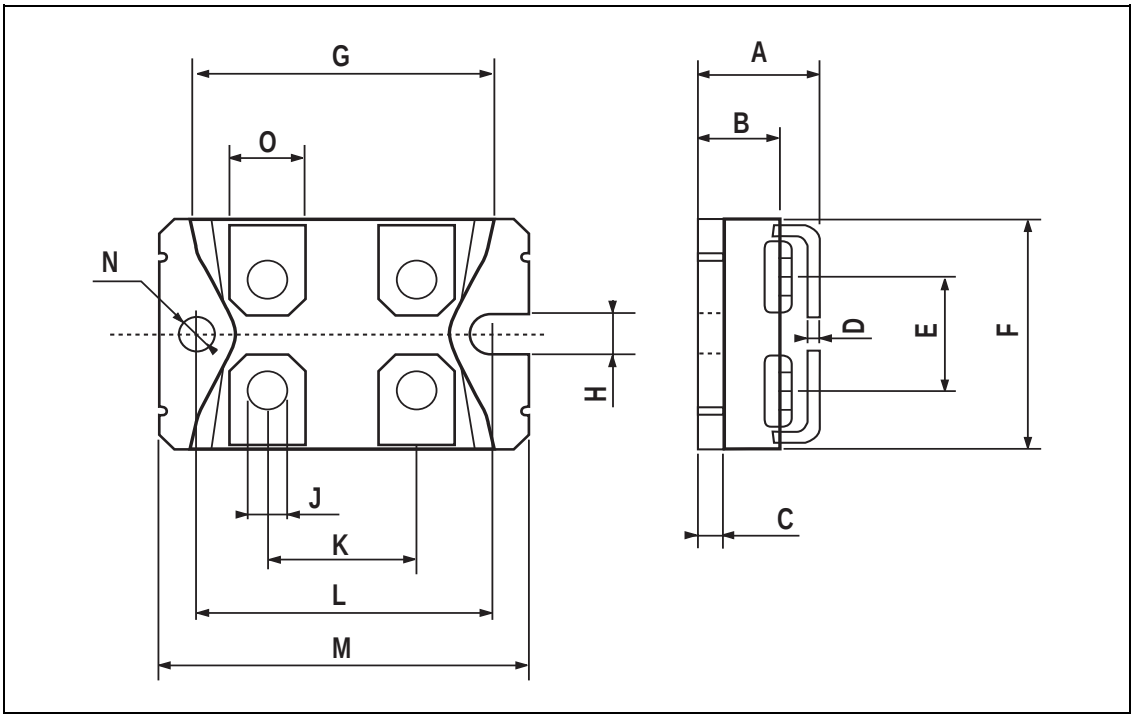


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



ISOTOP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.8		12.2	0.466		0.480
B	8.9		9.1	0.350		0.358
C	1.95		2.05	0.076		0.080
D	0.75		0.85	0.029		0.033
E	12.6		12.8	0.496		0.503
F	25.15		25.5	0.990		1.003
G	31.5		31.7	1.240		1.248
H	4			0.157		
J	4.1		4.3	0.161		0.169
K	14.9		15.1	0.586		0.594
L	30.1		30.3	1.185		1.193
M	37.8		38.2	1.488		1.503
N	4			0.157		
O	7.8		8.2	0.307		0.322



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